



isc Silicon PNP Power Transistor

DESCRIPTION

- DC Current Gain-
- : h_{FE}= 40@ I_C= -0.5A
- · Collector-Emitter Breakdown Voltage -
- : V_{(BR)CEO}= -100V(Min)
- Complement to type BD723
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

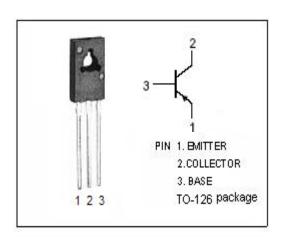
 Designed for use in audio output and general purpose amplifier applications.

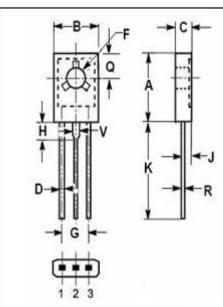
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| | 7.2002012 2 | | | | | |
|------------------|--|---------|------------|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | |
| V _{CBO} | Collector-Base Voltage | -100 | V | | | |
| V _{CEO} | Collector-Emitter Voltage | -100 | V | | | |
| V_{EBO} | Emitter-Base Voltage | -5 | V | | | |
| Ic | Collector Current-Continuous | -4 | Α | | | |
| Ісм | Collector Current-Peak | -7 | Α | | | |
| I _B | Base Current-Continuous | -1 | Α | | | |
| Pc | Collector Power Dissipation @ T _C =25 °C | 36 | W | | | |
| TJ | Junction Temperature | 150 | $^{\circ}$ | | | |
| T _{stg} | Storage Temperature Range | -65~150 | $^{\circ}$ | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--|-----|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 3.5 | °C/W |
| R _{th j-a} | th j-a Thermal Resistance, Junction to Ambient | | °C/W |





| | mm | |
|-----|-------|-------|
| DIM | MIN | MAX |
| Α | 10.70 | 10.95 |
| В | 7.70 | 7.90 |
| С | 2.60 | 2.80 |
| D | 0.66 | 0.86 |
| F | 3.10 | 3.30 |
| G | 4.48 | 4.68 |
| Н | 2.00 | 2.20 |
| J | 1.35 | 1.55 |
| K | 15.30 | 16.30 |
| Q | 3.70 | 3.90 |
| R | 0.40 | 0.60 |
| V | 1.17 | 1.37 |



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BD724

ELECTRICAL CHARACTERISTICS

 T_C =25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | |
|----------------------|--------------------------------------|--|------|------|------|------|--|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | Ic= -30mA ; I _B = 0 | -100 | | | V | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -2A; I _B = -0.2A | | | -1.0 | V | |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -2A; V _{CE} = -4V | | | -1.4 | V | |
| Ісво | Callegator Cutoff Current | V _{CB} = -100V; I _E = 0 | | | -50 | μА | |
| | Collector Cutoff Current | V _{CB} = -50V; I _E = 0; T _C = 150°C | | | -1 | mA | |
| I _{CEO} | Collector Cutoff Current | V _{CE} = -50V; I _B = 0 | | | -0.1 | mA | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -0.2 | mA | |
| h _{FE-1} | DC Current Gain | I _C = -0.5A; V _{CE} = -4V | 40 | | | | |
| h _{FE-2} | DC Current Gain | I _C = -2A; V _{CE} = -4V | 20 | | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = -0.5A; V _{CE} = -4V | 3 | | | MHz | |
| Switching Times | | | | | | | |
| t _{on} | Turn-On time | I _C = -1A; I _{B1} = -I _{B2} = -0.1A; | | 0.1 | | μs | |
| t _{off} | Turn-Off time | Vcc= -20V | | 0.4 | | μS | |

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